8-input NAND gate Rev. 4 — 22 July 2015

**Product data sheet** 

### 1. General description

The 74AHC30; 74AHCT30 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7-A.

The 74AHC30; 74AHCT30 provides an 8-input NAND function.

### 2. Features and benefits

- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V<sub>CC</sub>
- Input levels:
  - For 74AHC30: CMOS level
  - For 74AHCT30: TTL level
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

### 3. Ordering information

#### Table 1.Ordering information

Type number	Package				
	Temperature range	Name	Description	Version	
74AHC30D	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads;	SOT108-1	
74AHCT30D			body width 3.9 mm		
74AHC30PW	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads;	SOT402-1	
74AHCT30PW			body width 4.4 mm		
74AHC30BQ	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very	SOT762-1	
74AHCT30BQ			thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm		
74AHC30GU12	-40 °C to +125 °C	XQFN12	plastic, extremely thin quad flat package; no leads; 12 terminals; body $1.70 \times 2.00 \times 0.50$ mm	SOT1174-1	

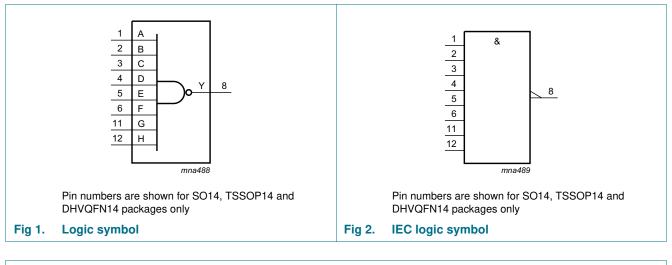


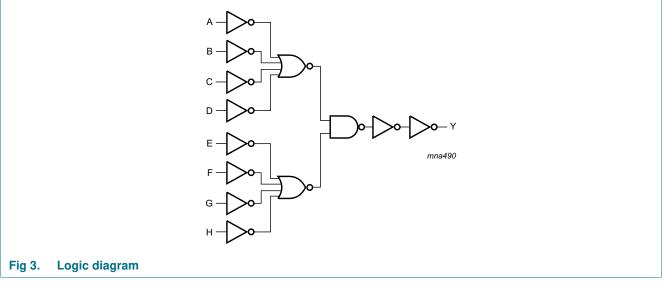
### 4. Marking

Table 2.         Marking codes	
Type number	Marking
74AHC30D	74AHC30D
74AHCT30D	74AHCT30D
74AHC30PW	AHC30
74AHCT30PW	AHCT30
74AHC30BQ	AHC30
74AHCT30BQ	AHT30
74AHC30GU12	A3[1]

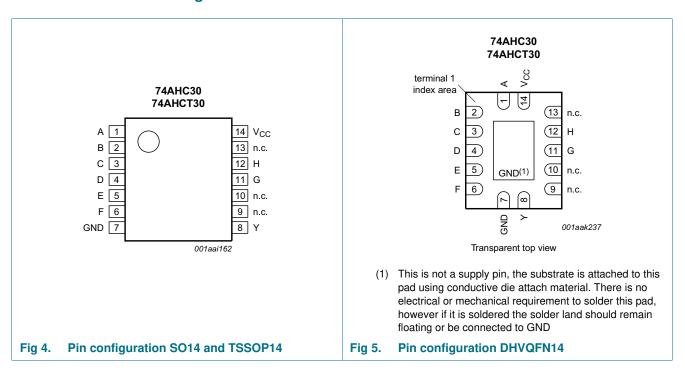
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 5. Functional diagram

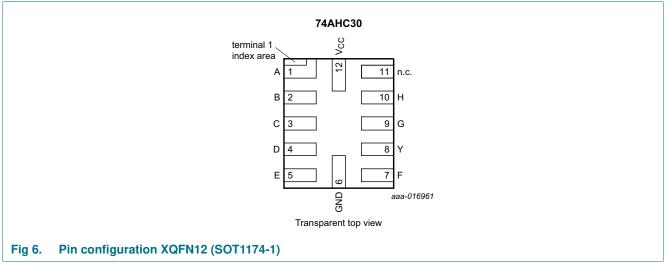




## 6. Pinning information







## 6.2 Pin description

Table 3.	Pin description		
Symbol	Pin		Description
	SO14, TSSOP14 and DHVQFN14	XQFN12	
A	1	1	data input
В	2	2	data input
С	3	3	data input
D	4	4	data input
E	5	5	data input
F	6	7	data input
GND	7	6	ground (0 V)
Y	8	8	data output
n.c.	9	-	not connected
n.c.	10	-	not connected
G	11	9	data input
Н	12	10	data input
n.c.	13	11	not connected
V <sub>CC</sub>	14	12	supply voltage

## 7. Functional description

#### Table 4. Function table<sup>[1]</sup>

Input								Output
Α	В	С	D	E	F	G	Н	Y
L	Х	Х	Х	Х	Х	Х	Х	Н
Х	L	Х	Х	Х	Х	Х	Х	Н
Х	Х	L	Х	Х	Х	Х	Х	Н
Х	Х	Х	L	Х	Х	Х	Х	Н
Х	Х	Х	Х	L	Х	Х	Х	Н
Х	Х	Х	Х	Х	L	Х	Х	Н
Х	Х	Х	Х	Х	Х	L	Х	Н
Х	Х	Х	Х	Х	Х	Х	L	Н
Н	Н	Н	Н	Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC</sub>	supply voltage			-0.5	+7.0	V
VI	input voltage			-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V	[1]	-20	-	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC}$ + 0.5 V	[1]	-20	+20	mA
lo	output current	$V_{O} = -0.5 \text{ V}$ to ( $V_{CC} + 0.5 \text{ V}$ )		-25	+25	mA
I <sub>CC</sub>	supply current			-	+75	mA
I <sub>GND</sub>	ground current			-75	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$				
		SO14, TSSOP14 and DHVQFN14	[2]	-	500	mW
		XQFN12		-	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For SO14 packages: above 70 °C, the value of P<sub>tot</sub> derates linearly at 8 mW/K.
 For TSSOP14 packages: above 60 °C, the value of P<sub>tot</sub> derates linearly at 5.5 mW/K.
 For DHVQFN14 packages: above 60 °C, the value of P<sub>tot</sub> derates linearly at 4.5 mW/K.

## 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-	74AHC30			74AHCT30		
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	0	-	5.5	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC}=3.3~V\pm0.3~V$	-	-	100	-	-	-	ns/V
	and fall rate	$V_{CC}=5.0~V\pm0.5~V$	-	-	20	-	-	20	ns/V

## **10. Static characteristics**

#### Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C	;	–40 °C t	o +85 °C	–40 °C to +125 °C		Unit	
			Min	Тур	Max	Min	Max	Min	Max	-	
74AHC3	0	1				1		1	1		
VIH	HIGH-level	V <sub>CC</sub> = 2.0 V	1.5	-	-	1.5	-	1.5	-	V	
	input voltage	V <sub>CC</sub> = 3.0 V	2.1	-	-	2.1	-	2.1	-	V	
		V <sub>CC</sub> = 5.5 V	3.85	-	-	3.85	-	3.85	-	V	
V <sub>IL</sub>	LOW-level	V <sub>CC</sub> = 2.0 V	-	-	0.5	-	0.5	-	0.5	V	
	input voltage	V <sub>CC</sub> = 3.0 V	-	-	0.9	-	0.9	-	0.9	V	
		V <sub>CC</sub> = 5.5 V	-	-	1.65	-	1.65	-	1.65	V	
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$									
	output voltage	$I_{O} = -50 \ \mu A; V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V	
		$I_{O} = -50 \ \mu A; V_{CC} = 3.0 \ V$	2.9	3.0	-	2.9	-	2.9	-	V	
		$I_{O} = -50 \ \mu A; V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	4.4	-	V	
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V	
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V	
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$									
	output voltage	$I_{O} = 50 \ \mu A; V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 50 \ \mu A; \ V_{CC} = 3.0 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 50 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	-	0.1	V	
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V	
		$I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V	
lı	input leakage current	$V_{I} = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μA	
I <sub>CC</sub>	supply current		-	-	2.0	-	20	-	40	μA	
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF	
Co	output capacitance		-	4	-	-	-	-	-	pF	

8-input NAND gate

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit		
			Min	Тур	Max	Min	Max	Min	Max			
74AHCT	30	1										
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V		
V <sub>IL</sub>	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V		
V <sub>OH</sub>	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$									
	output voltage	I <sub>O</sub> = -50 μA	4.4	4.5	-	4.4	-	4.4	-	V		
		I <sub>O</sub> = -8.0 mA	3.94	-	-	3.80	-	3.70	-	V		
V <sub>OL</sub>	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$										
	output voltage	I <sub>O</sub> = 50 μA	-	0	0.1	-	0.1	-	0.1	V		
		l <sub>O</sub> = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V		
I	input leakage current	$V_1 = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$	-	-	0.1	-	1.0	-	2.0	μA		
I <sub>CC</sub>	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	2.0	-	20	-	40	μA		
Δl <sub>CC</sub>	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}$ ; other pins at $V_{CC}$ or GND; $I_O = 0 \text{ A}$ ; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA		
Cı	input capacitance	$V_I = V_{CC}$ or GND	-	3	10	-	10	-	10	pF		
Co	output capacitance		-	4	-	-	-	-	-	pF		

#### Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

## **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	Min	Мах	
74AHC3	0	1								
t <sub>pd</sub> propagation	A, B, C, D, E, F, G, H to Y; see Figure 7 and 8 [2]									
	delay	V <sub>CC</sub> = 3.0 V to 3.6 V								
		C <sub>L</sub> = 15 pF	-	5.0	9.5	1.0	11.0	1.0	12.0	ns
	l	C <sub>L</sub> = 50 pF	-	6.7	12.0	1.0	14.5	1.0	15.5	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V								
		C <sub>L</sub> = 15 pF	-	3.6	6.5	1.0	7.5	1.0	8.0	ns
		C <sub>L</sub> = 50 pF	-	4.9	8.0	1.0	9.5	1.0	10.5	ns
C <sub>PD</sub>	power dissipation capacitance	$      f_i = 1 \text{ MHz}; \qquad [3] \\ V_I = \text{GND to } V_{CC} $	-	10	-	-	-	-	-	pF

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8-input NAND gate

#### Table 8. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 8</u>.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit	
			Min	Typ[1]	Max	Min	Max	Min	Max	]	
74AHCT	30; V <sub>CC</sub> = 4.5 '	V to 5.5 V									
t <sub>pd</sub>	propagation	A, B, C, D, E, F, G, H to Y; see Figure 7 and 8 2									
	delay	C <sub>L</sub> = 15 pF	-	3.3	6.5	1.0	7.5	1.0	8.0	ns	
		C <sub>L</sub> = 50 pF	-	4.7	8.5	1.0	9.5	1.0	10.5	ns	
C <sub>PD</sub>	power dissipation capacitance	$      f_i = 1 \text{ MHz}; \qquad \qquad \boxed{3} \\ V_I = \text{GND to } V_{CC} $	-	12	-	-	-	-	-	pF	

[1] Typical values are measured at nominal supply voltage ( $V_{CC} = 3.3$  V and  $V_{CC} = 5.0$  V).

#### [2] $t_{pd}$ is the same as $t_{PLH}$ and $t_{PHL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$ 

 $f_i = input frequency in MHz;$ 

 $f_o = output$  frequency in MHz;

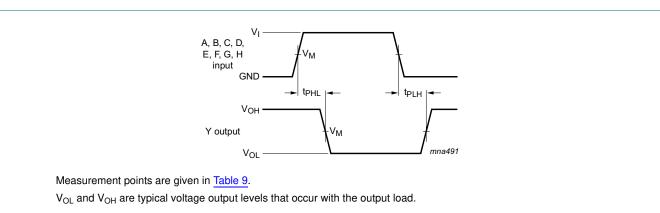
 $C_L$  = output load capacitance in pF;

 $V_{CC}$  = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 12. Waveforms



#### Fig 7. Input to output propagation delays

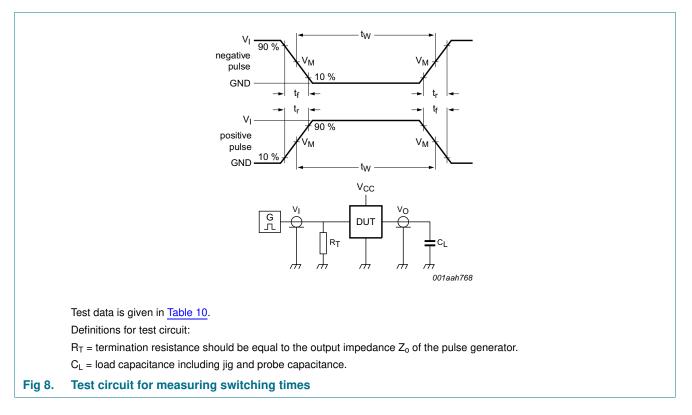
#### Table 9.Measurement points

Туре	Input	Output
	V <sub>M</sub>	V <sub>M</sub>
74AHC30	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74AHCT30	1.5 V	$0.5 \times V_{CC}$

#### **NXP Semiconductors**

## 74AHC30; 74AHCT30

#### 8-input NAND gate

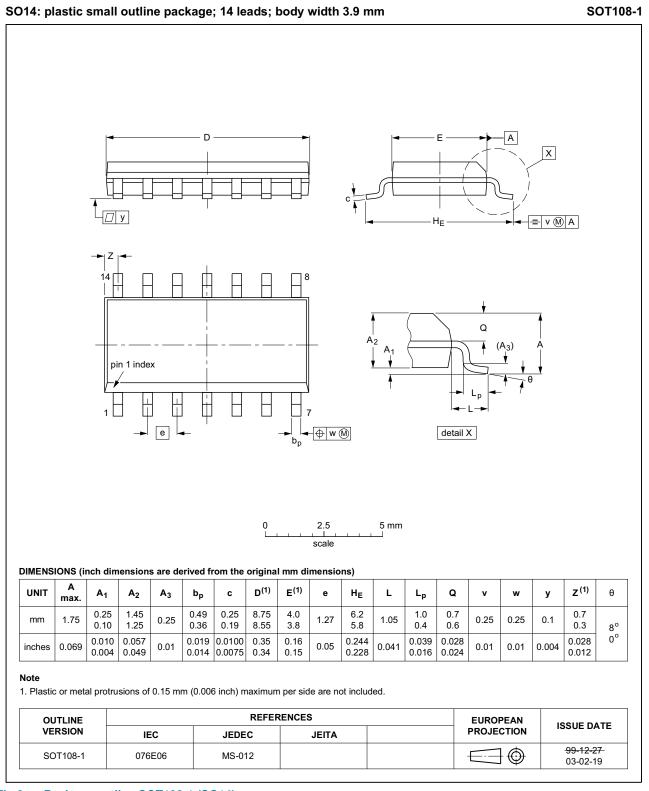


#### Table 10. Test data

Туре	Input		Load	Test
	VI	t <sub>r</sub> , t <sub>f</sub>	CL	
74AHC30	V <sub>CC</sub>	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>
74AHCT30	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t <sub>PLH</sub> , t <sub>PHL</sub>

8-input NAND gate

## 13. Package outline



#### Fig 9. Package outline SOT108-1 (SO14)

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Product data sheet

8-input NAND gate

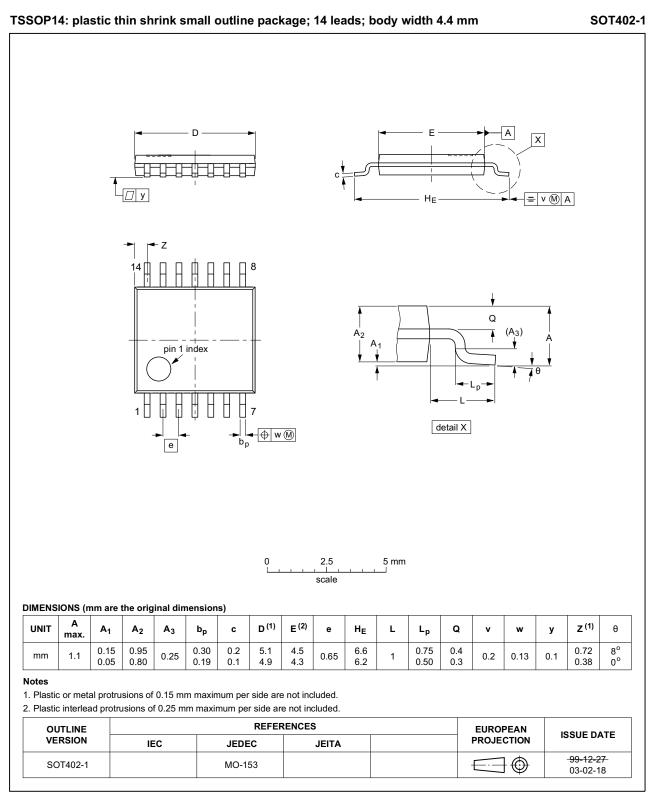
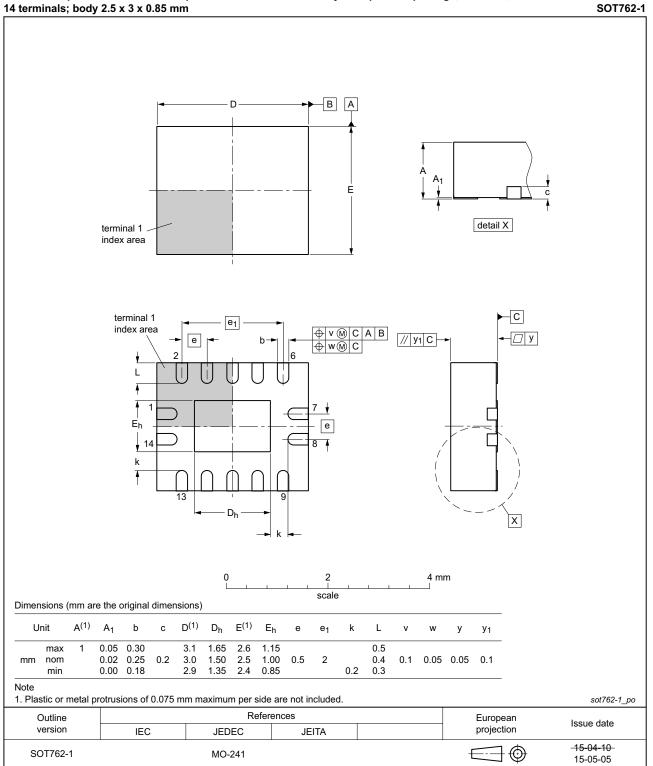


Fig 10. Package outline SOT402-1 (TSSOP14)

8-input NAND gate

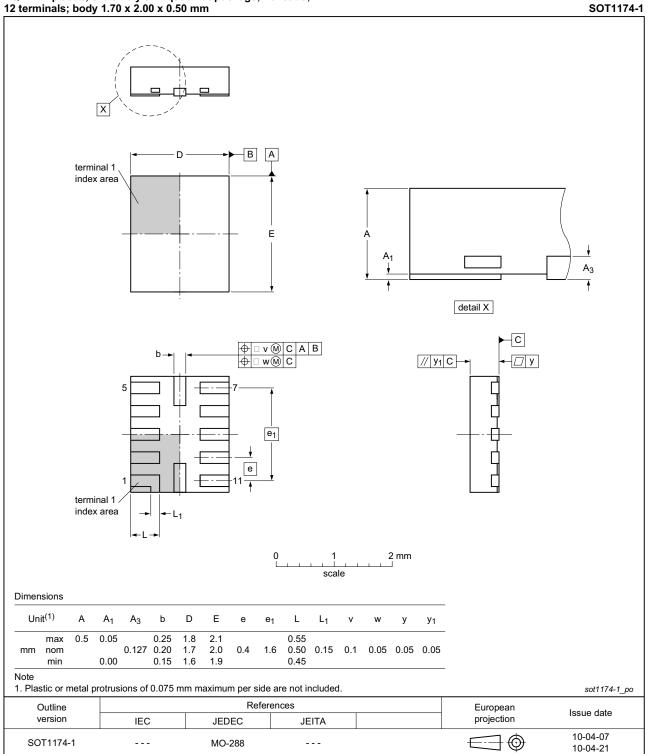


DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;

#### Fig 11. Package outline SOT762-1 (DHVQFN14)

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8-input NAND gate



XQFN12: plastic, extremely thin quad flat package; no leads; 12 terminals; body 1.70 x 2.00 x 0.50 mm

Fig 12. Package outline SOT1174-1 (XQFN12)

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## 14. Abbreviations

Table 11. Abbreviations			
Acronym	Description		
CDM	Charged Device Model		
CMOS	Complementary Metal-Oxide Semiconductor		
DUT	Device Under Test		
ESD	ElectroStatic Discharge		
HBM	Human Body Model		
LSTTL	Low-power Schottky Transistor-Transistor Logic		
ММ	Machine Model		

## **15. Revision history**

#### Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74AHC_AHCT30 v.4	20150722	Product data sheet	-	74AHC_AHCT30 v.3	
Modifications:	Added type number 74AHC30GU12.				
74AHC_AHCT30 v.3	20090626	Product data sheet	-	74AHC_AHCT30 v.2	
Modifications: • Section 3: DHVQFN14 package added.					
	<u>Section 8</u> : derating values added for DHVQFN14 package.				
	• <u>Section 13</u> : c	utline drawing added for DHV	QFN14 package.		
74AHC_AHCT30 v.2	20080530	Product data sheet	-	74AHC_AHCT30 v.1	
74AHC_AHCT30 v.1	19991130	Product specification	-	-	

## 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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74AHC AHCT30

#### 8-input NAND gate

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